MSKSEMI















ESD

TVS

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Broduct data sheet

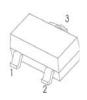


Semiconductor





SOT - 23



- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

TRANSISTOR (NPN)

FEATURES

- High breakdown voltage
- Low collector-emitter saturation voltage
- Complementary to MMBTA92-MS (PNP)

Marking: 1D

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

| Symbol | Parameter | Value | Unit |
|----------------------------------|---|----------|---------------|
| V _{CBO} | Collector-Base Voltage | 300 | V |
| V _{CEO} | Collector-Emitter Voltage | 300 | V |
| V _{EBO} | Emitter-Base Voltage | 5 | V |
| Ic | Collector Current -Continuous | 0.3 | Α |
| I _{CM} | Collector Current-Peak | 0.5 | А |
| Pc | Collector Power dissipation | 0.35 | W |
| R _{OJA} | Thermal Resistance, junction to Ambient | 357 | °C/W |
| T _J ,T _{stg} | Operation Junction and Storage Temperature Range | -55~+150 | ${\mathbb C}$ |

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

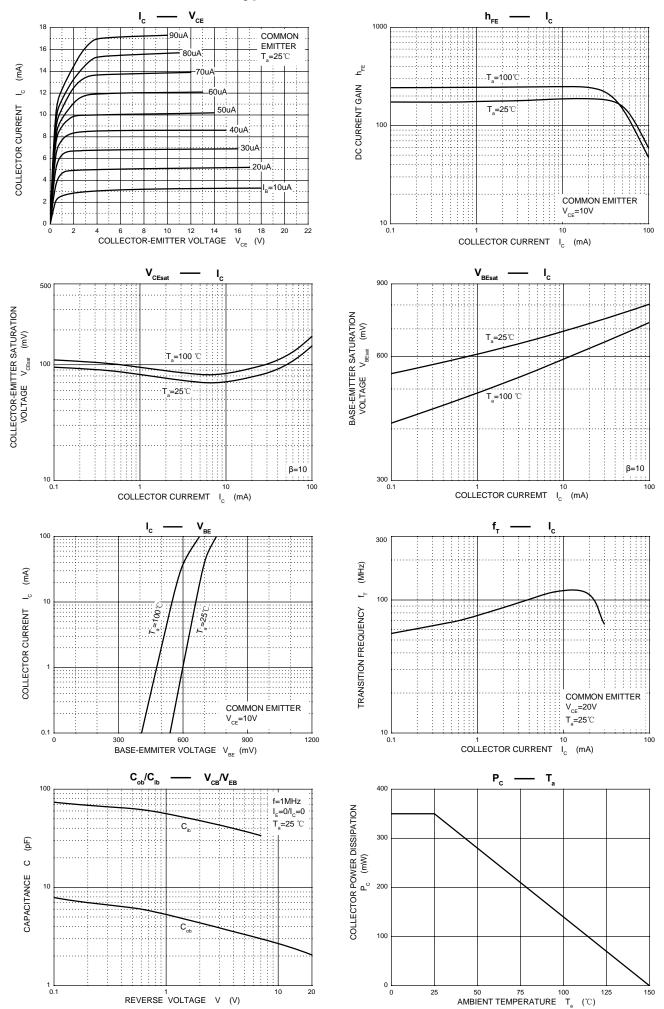
| Parameter | Symbol | Test conditions | Min | Max | Unit | | |
|--------------------------------------|-----------------------|---|-----|------|---------|--|--|
| Collector-base breakdown voltage | V _{(BR)CBO} | I _C = 100μΑ,I _E =0 | 300 | | V | | |
| Collector-emitter breakdown voltage | V _{(BR)CEO} | I _C = 1mA, I _B =0 | 300 | | V | | |
| Emitter-base breakdown voltage | V _{(BR)EBO} | I _E = 100μA, I _C =0 | 5 | | ٧ | | |
| Collector cut-off current | I _{CBO} | V _{CB} =200V, I _E =0 | | 0.25 | μΑ | | |
| Emitter cut-off current | I _{EBO} | V_{EB} = 5V, I_{C} =0 | | 0.1 | μA | | |
| | h _{FE(1)} | V _{CE} = 10V, I _C = 1mA | 60 | | | | |
| DC current gain | h _{FE(2)} | V _{CE} = 10V, I _C =10mA | 100 | 200 | | | |
| | h _{FE(3)} | V _{CE} =10V, I _C =30mA | 60 | | | | |
| Collector-emitter saturation voltage | V _{CE} (sat) | I _C =20mA, I _B = 2mA | | 0.2 | V | | |
| Base-emitter saturation voltage | V _{BE} (sat) | I _C = 20mA, I _B =2mA | | 0.9 | V | | |
| Transition frequency | f⊤ | V _{CE} = 20V, I _C = 10mA, | 50 | | MHz | | |
| Transition frequency | | f=30MHz | 30 | | 1411 12 | | |



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Compiance

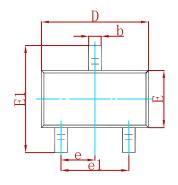
Typical Characteristics

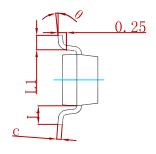


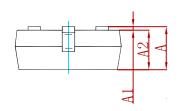


Semiconductor Compiance

PACKAGE MECHANICAL DATA

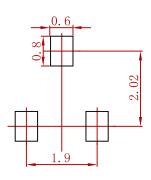






| Cumhal | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| Symbol | Min | Max | Min | Max |
| Α | 0.900 | 1.150 | 0.035 | 0.045 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.900 | 1.050 | 0.035 | 0.041 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| С | 0.080 | 0.150 | 0.003 | 0.006 |
| D | 2.800 | 3.000 | 0.110 | 0.118 |
| E | 1.200 | 1.400 | 0.047 | 0.055 |
| E1 | 2.250 | 2.550 | 0.089 | 0.100 |
| е | 0.950 |) TYP | 0.037 | 7 TYP |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.550 REF | | 0.022 REF | |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 |
| θ | 0° | 8° | 0° | 8° |

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

REEL SPECIFICATION

| P/N | PKG | QTY |
|------------|--------|------|
| MMBTA42-MS | SOT-23 | 3000 |



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